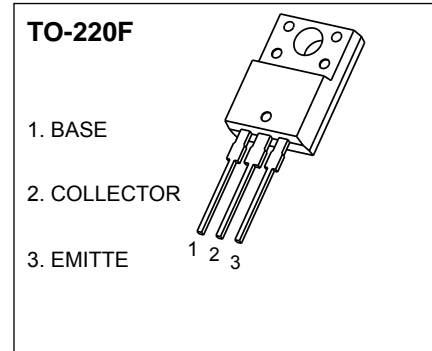


TO-220F Plastic-Encapsulate Transistors

KSA614F TRANSISTOR (PNP)

FEATURE

- Low Frequency Amplifier
- Medium Speed Switching



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-55	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-3	A
P _C	Collector Dissipation	2	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 to +150	°C

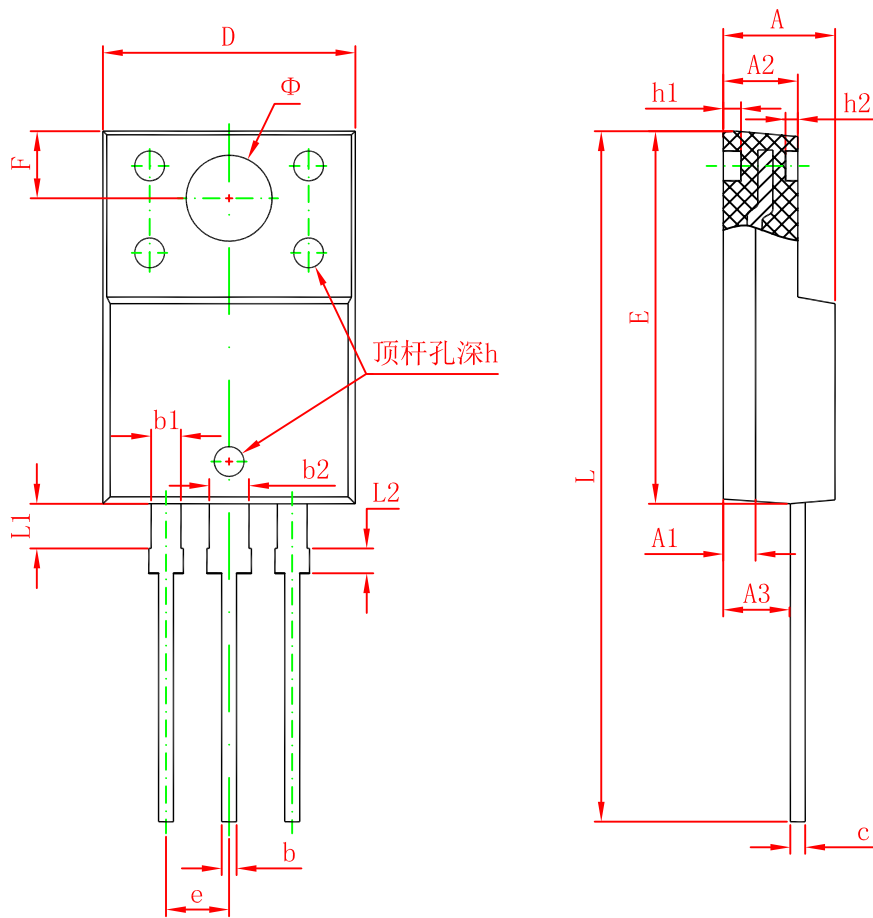
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C = -500μA, I _E =0	-80			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = -10mA, I _B =0	-55			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = -500μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50 V, I _E =0			-50	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-50	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C = -500mA	40		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -1 A, I _B = -100mA			-0.5	V

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240

TO-220F Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.500 REF.		0.138 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	0.900	1.100	0.035	0.043